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# Lecture5: Diode (3)

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# IV characteristics (1)

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- Review
  - The diode current,  $I_D$ , is dependent on the diode voltage,  $V_D$ .
  - Then, what is  $I_D(V_D)$ ?
- Compare  $V_D = 0.3 \text{ V}$ ,  $0.4 \text{ V}$ , and  $0.5 \text{ V}$ .
  - We know that the electric field for  $0.5 \text{ V}$  is weakest.
  - Of course, for  $0.3 \text{ V}$ , it is strongest.
  - Anyway, they are different by a constant voltage,  $0.1 \text{ V}$ .
  - Then, what about  $I_D(0.3)$ ,  $I_D(0.4)$ , and  $I_D(0.5)$ ?
  - Do you expect a linear dependence?

# IV characteristics (2)

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- Exponential dependence on  $V_D$ 
  - $V_D$  is normalized by the thermal voltage,  $V_T = \frac{k_B T}{q}$ .
  - At 300 K,  $V_T \approx 0.002585 \text{ V} = 25.85 \text{ mV}$ .
  - Then, the diode current can be written as
$$I_D = I_S \left( \exp \frac{V_D}{V_T} - 1 \right)$$
  - Here, the “reverse saturation current” ( $I_S$ ) is a given constant. It’s a small current.

# IV characteristics (3)

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- Some limiting cases:

$$I_D = I_S \left( \exp \frac{V_D}{V_T} - 1 \right)$$

- When  $V_D$  is close to zero,  $\exp \frac{V_D}{V_T} \approx 1 + \frac{V_D}{V_T}$

$$I_D = I_S \frac{V_D}{V_T}$$

- When  $V_D$  is negative and  $V_D \ll -V_T$ ,  $\exp \frac{V_D}{V_T} \approx 0$

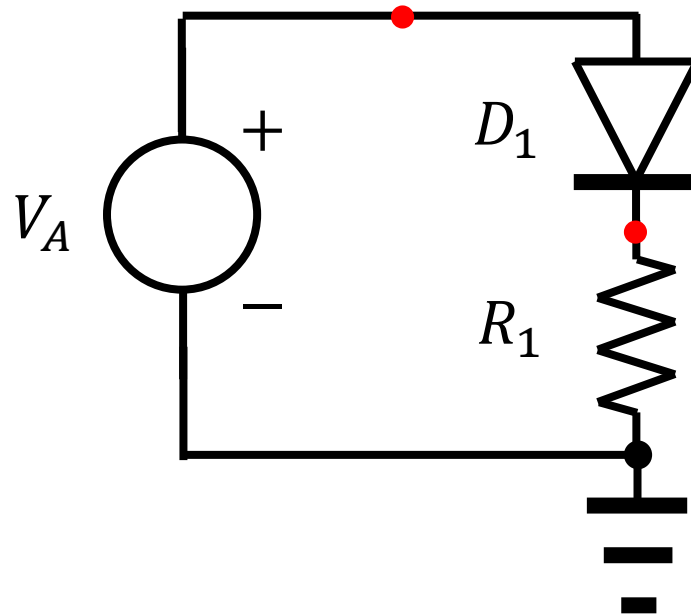
$$I_D = -I_S$$

- When  $V_D$  is positive and  $V_D \gg V_T$ ,  $I_D = I_S \exp \frac{V_D}{V_T}$

# General solution (1)

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- Analyze the following circuit. (A diode-resistor combination)
  - Calculation of node voltages and terminal currents



# General solution (2)

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- Identify the nodes and apply the KCL.

- Two nodes (red dots) are found.

$$I_V + I_D = 0$$

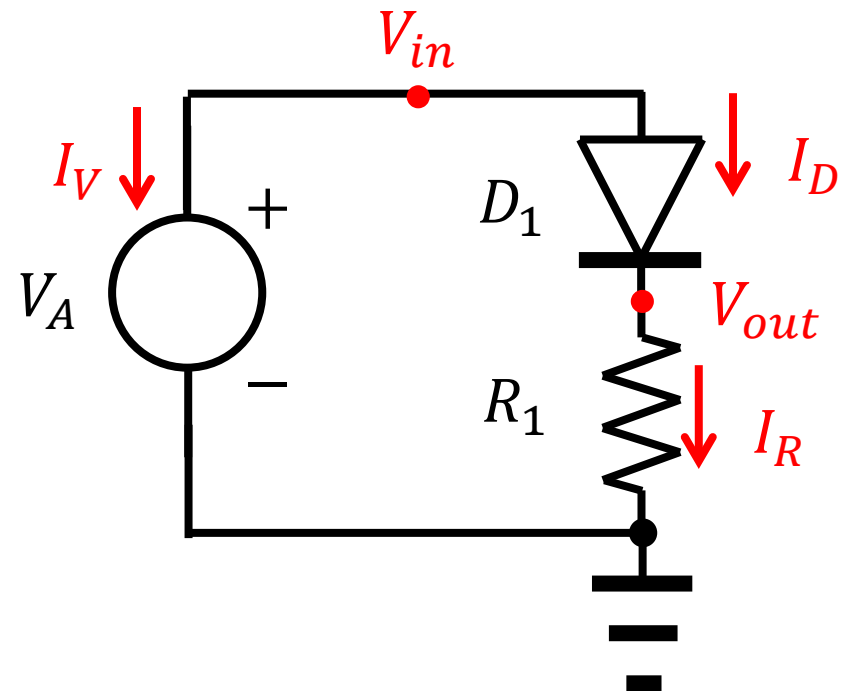
$$-I_D + I_R = 0$$

- Equations for terminal IVs

$$V_{in} = V_A$$

$$I_D = I_S \left( \exp \left( \frac{V_{in} - V_{out}}{V_T} \right) - 1 \right)$$

$$I_R = \frac{V_{out}}{R_1}$$



# General solution (3)

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- Solve the set of equations.
  - After simple manipulation, it is easily found that
$$-I_S \left( \exp \left( \frac{V_A - V_{out}}{V_T} \right) - 1 \right) + \frac{V_{out}}{R_1} = 0$$
  - An nonlinear equation for  $V_{out}$  is obtained.
  - The solution,  $V_{out}$ , can be visualized by drawing the following two curves.

$$y = I_S \left( \exp \left( \frac{V_A - x}{V_T} \right) - 1 \right)$$
$$y = \frac{x}{R_1}$$

# Graphical solution (1)

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- Assume that  $V_A = 2\text{ V}$ ,  $I_S = 0.5\text{ fA}$ , and  $R_1 = 270\text{ }\Omega$ .

- Draw two curves:

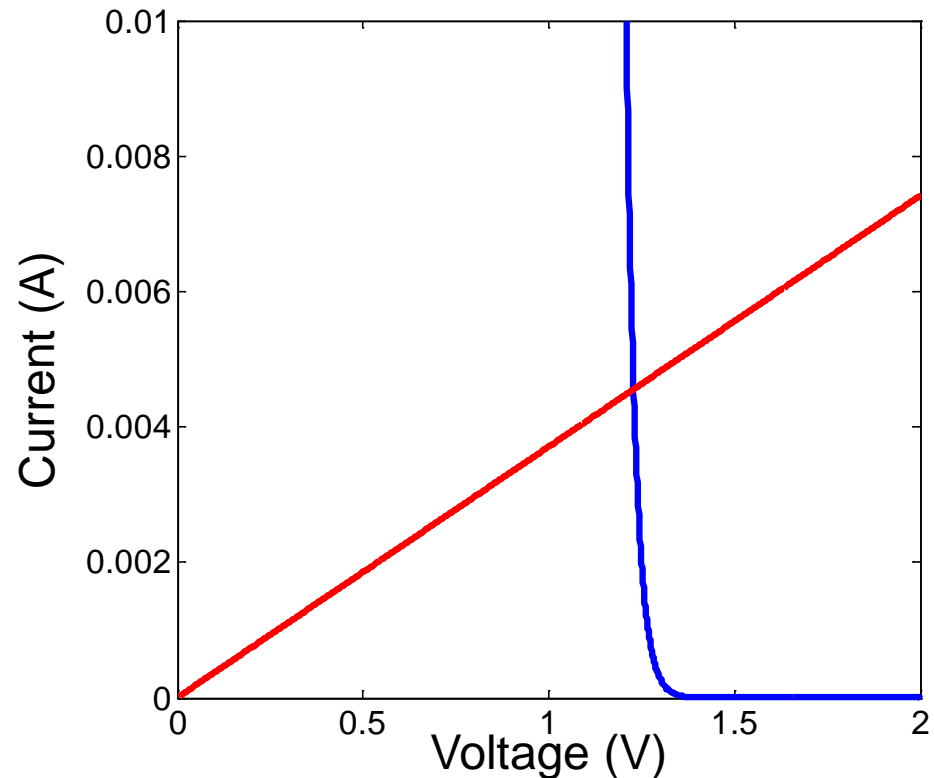
$$y = I_S \left( \exp \left( \frac{V_A - x}{V_T} \right) - 1 \right)$$

$$y = \frac{x}{R_1}$$

- The answer is

$$V_{out} = 1.2287\text{ V}.$$

- 0.77 V is applied to the diode.

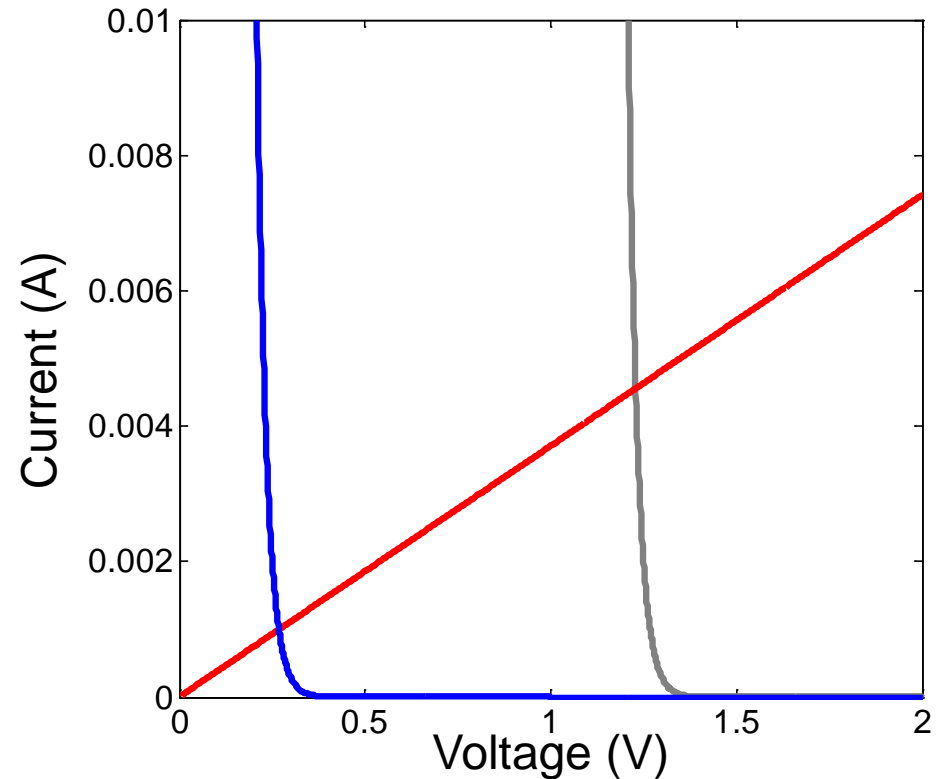




# Graphical solution (2)

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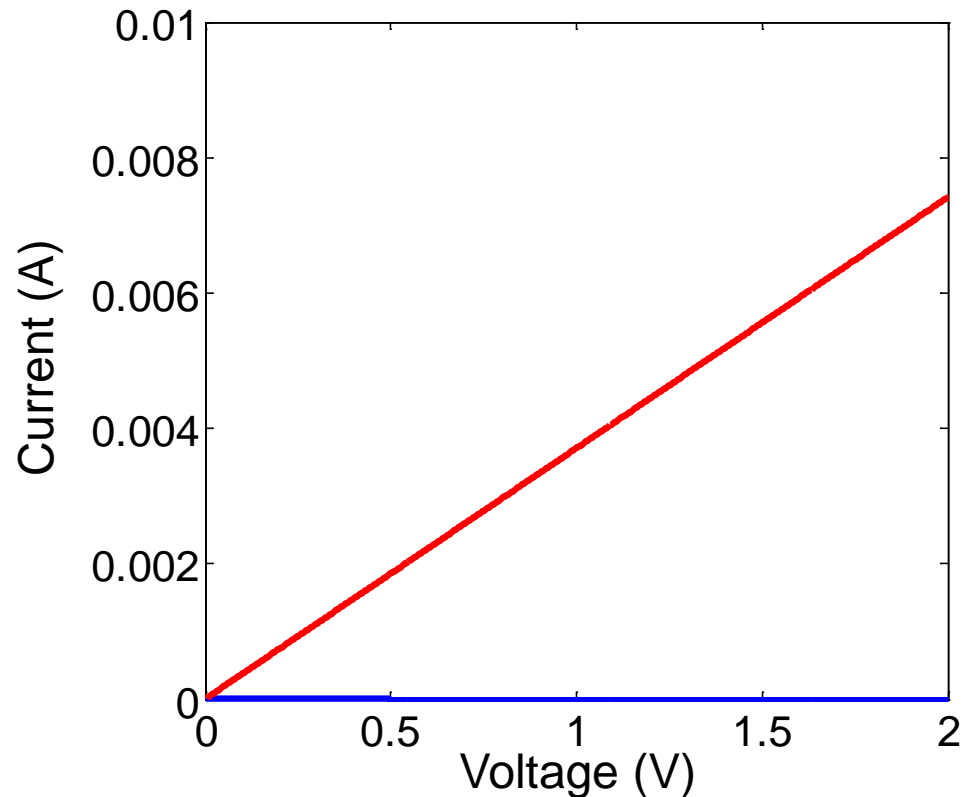
- Reduce  $V_A$  to 1 V.
  - The answer is  $V_{out} = 0.2687$  V.
  - 0.73 V is applied to the diode.
- Even smaller  $V_A$ ?
  - For example, 0.5 V?



# When $V_A = 0.5 \text{ V}$

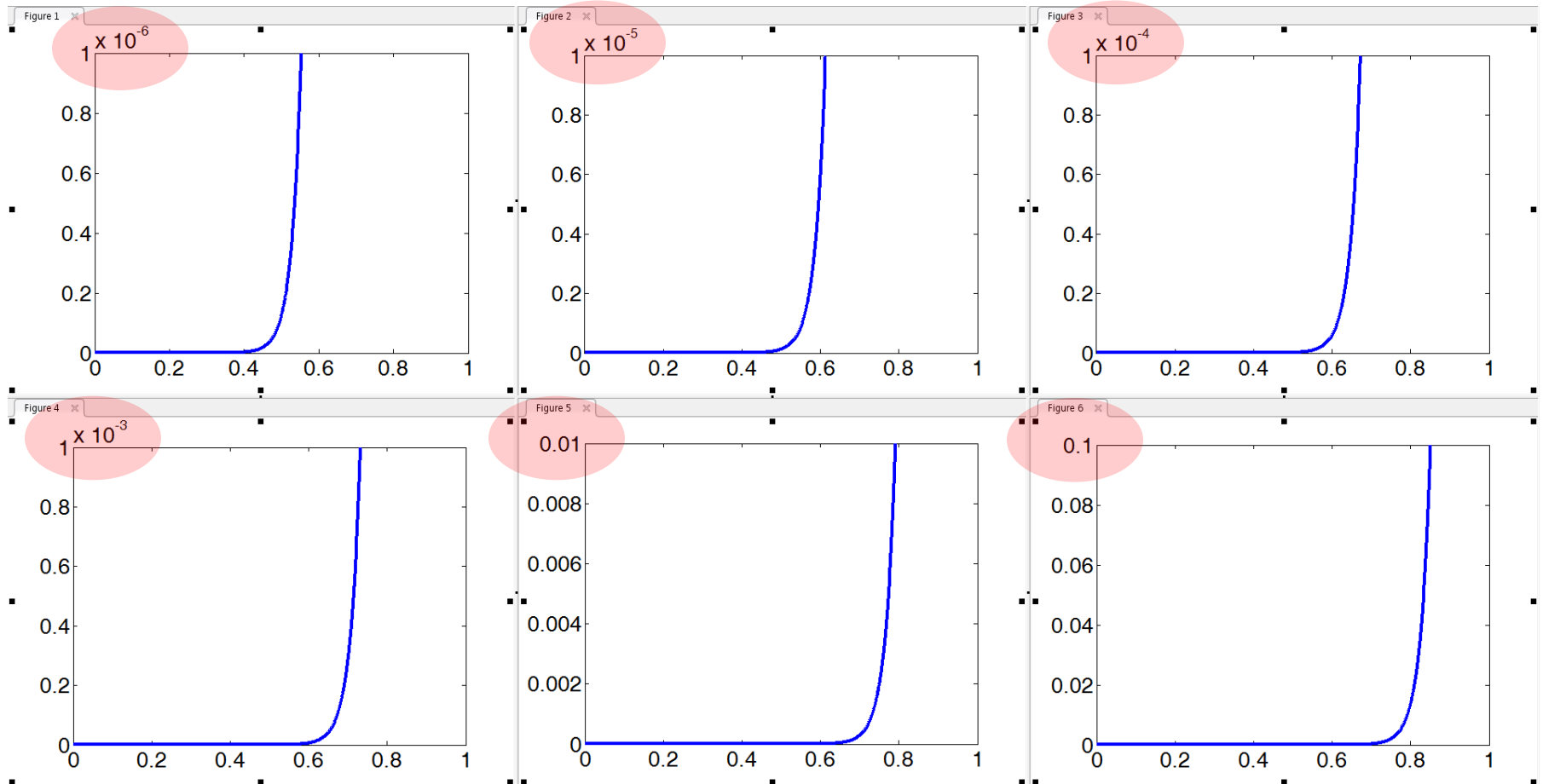
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- The same scale as before.
  - ???
  - What is  $V_{out}$ ?
- Not enough  $V_A$ 
  - No current conduction



# Diode IV curves

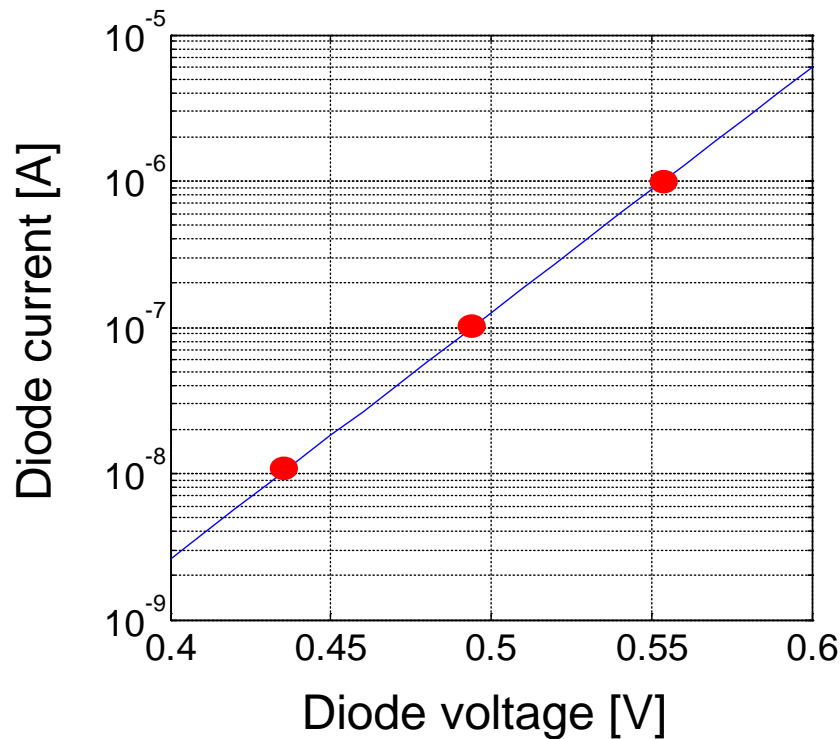
- A diode with  $I_S = 5 \times 10^{-16} \text{ A}$  (Only different  $y$  scales)



# Important observation

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- In order to obtain 10x large current,
  - We must apply only 60 mV additionally. (300K)



# Diode model

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- Two phases

